

MCP1703

250 mA, 16V, Low Quiescent Current

Features

- 2.0 µA Typical Quiescent Current
- Input Operating Voltage Range: 2.7V to16.0V
- 250 mA Output Current for Output Voltages ≥ 2.5V
- 200 mA Output Current for Output Voltages < 2.5V
- Low Drop Out Voltage, 625 mV typical @ 250 mA for V_R = 2.8V
- 0.4% Typical Output Voltage Tolerance
- Standard Output Voltage Options (1.2V, 1.5V, 1.8V, 2.5V, 2.8V, 3.0V, 3.3V, 4.0V, 5.0V)
- Output voltage range 1.2V to 5.5V in 0.1V increments (50 mV increments available upon request)
- Stable with 1.0 μF to 22 μF output capacitance
- Short-Circuit Protection
- · Overtemperature Protection

Applications

- · Battery-powered Devices
- · Battery-powered Alarm Circuits
- Smoke Detectors
- CO² Detectors
- · Pagers and Cellular Phones
- · Smart Battery Packs
- · Low Quiescent Current Voltage Reference
- PDAs
- Digital Cameras
- · Microcontroller Power
- Solar-Powered Instruments
- · Consumer Products
- · Battery Powered Data Loggers

Description

The MCP1703 is a family of CMOS low dropout (LDO) voltage regulators that can deliver up to 250 mA of current while consuming only 2.0 μ A of quiescent current (typical). The input operating range is specified from 2.7V to 16.0V, making it an ideal choice for two to six primary cell battery-powered applications, 9V alkaline and one or two cell Li-lon-powered applications.

The MCP1703 is capable of delivering 250 mA with only 625 mV (typical) of input to output voltage differential (V_{OUT} = 2.8V). The output voltage tolerance of the MCP1703 is typically ±0.4% at +25°C and ±3% maximum over the operating junction temperature range of -40°C to +125°C. Line regulation is ±0.1% typical at +25°C.

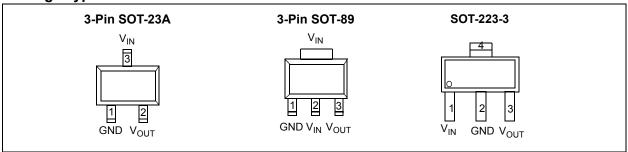
Output voltages available for the MCP1703 range from 1.2V to 5.5V. The LDO output is stable when using only 1 μ F of output capacitance. Ceramic, tantalum or aluminum electrolytic capacitors can all be used for input and output. Overcurrent limit and overtemperature shutdown provide a robust solution for any application.

Package options include the SOT-223-3, SOT-23A, and SOT-89-3.

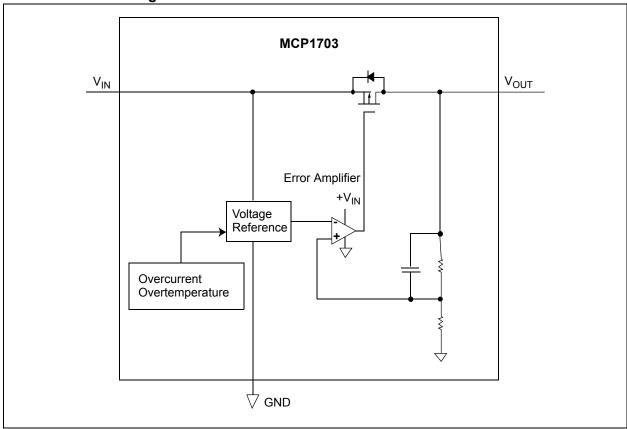
Related Literature

- AN765, "Using Microchip's Micropower LDOs", DS00765, Microchip Technology Inc., 2002
- AN766, "Pin-Compatible CMOS Upgrades to BiPolar LDOs", DS00766, Microchip Technology Inc., 2002
- AN792, "A Method to Determine How Much Power a SOT23 Can Dissipate in an Application", DS00792, Microchip Technology Inc., 2001

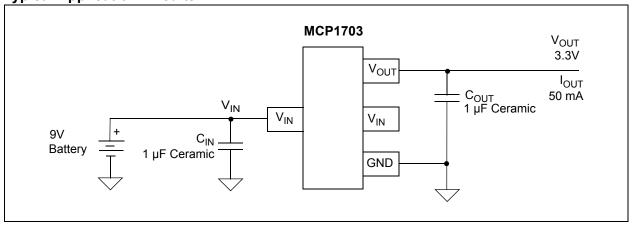
Package Types



Functional Block Diagrams



Typical Application Circuits



1.0 **ELECTRICAL CHARACTERISTICS**

Absolute Maximum Ratings †

V _{DD}	+18V
All inputs and outputs w.r.t(V_{SS} -0.3V) to (V_{IN} +0.3V)
Peak Output Current	500 mA
Storage temperature	65°C to +150°C
Maximum Junction Temperature	+150°C
Operating Junction Temperature	40°C to +125°C
ESD protection on all pins (HBM;MM))≥ 4 kV; ≥ 400V

† Notice: Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

DC CHARACTERISTICS

Electrical Specifications: Unless otherwise specified, all limits are established for V_{IN} = V_{OUT(MAX)} + V_{DROPOUT(MAX)}, Note 1, I_{LOAD} = 100 μA , C_{OUT} = 1 μF (X7R), C_{IN} = 1 μF (X7R), T_A = +25°C.

Boldface type applies for junction temperatures, T₁ (**Note 7**) of -40°C to +125°C.

Parameters	Symbol	Min	Тур	Max	Units	Conditions		
Input / Output Characteristics								
Input Operating Voltage	V _{IN}	2.7	_	16.0	V	Note 1		
Input Quiescent Current	Iq	_	2.0	5	μΑ	I _L = 0 mA		
Maximum Output Current	I _{OUT_mA}	250	_	_	mA	For V _R ≥ 2.5V		
	_	50	100	_	mA	For V_R < 2.5V, $V_{IN} \ge 2.7V$		
		100	130	_	mA	For V _R < 2.5V, V _{IN} ≥ 2.95V		
		150	200	_	mA	For V_R < 2.5V, $V_{IN} \ge 3.2V$		
		200	250	_	mA	For V_R < 2.5V, $V_{IN} \ge 3.45V$		
Output Short Circuit Current	l _{out_sc}	_	400	-	mA	V _{IN} = V _{IN(MIN)} (Note 1), V _{OUT} = GND, Current (average current) measured 10 ms after short is applied.		
Output Voltage Regulation	V _{OUT}	V_R-3.0% V _R -2.0%	V _R ±0.4 %	V_R+3.0% V _R +2.0%	V	Note 2		
V _{OUT} Temperature Coefficient	TCV _{OUT}	_	50	150	ppm/°C	Note 3		
Line Regulation	ΔV _{OUT} / (V _{OUT} XΔV _{IN})	-0.3	±0.1	+0.3	%/V	$(V_{OUT(MAX)} + V_{DROPOUT(MAX)}) \le V_{IN}$ $\le 16V$, Note 1		
Load Regulation	$\Delta V_{OUT}/V_{OUT}$	-2.5	±1.0	+2.5	%	I_L = 1.0 mA to 250 mA for V_R >= 2.5V I_L = 1.0 mA to 200 mA for V_R < 2.5V V_{IN} = 3.65V, Note 4		

- Note 1: The minimum V_{IN} must meet two conditions: $V_{IN} \ge 2.7V$ and $V_{IN} \ge (V_{OUT(MAX)} + V_{DROPOUT(MAX)})$.
 - V_R is the nominal regulator output voltage. For example: V_R = 1.2V, 1.5V, 1.8V, 2.5V, 2.8V, 3.0V, 3.3V, 4.0V, or 5.0V.
 - The input voltage V_{IN} = $V_{OUT(MAX)}$ + $V_{DROPOUT(MAX)}$ or Vi_{IN} = 2.7V (whichever is greater); I_{OUT} = 100 μ A. TCV_{OUT} = ($V_{OUT-HIGH}$ $V_{OUT-LOW}$) *10⁶ / (V_R * Δ Temperature), $V_{OUT-HIGH}$ = highest voltage measured over the temperature) ature range. V_{OUT-LOW} = lowest voltage measured over the temperature range.
 - Load regulation is measured at a constant junction temperature using low duty cycle pulse testing. Changes in output 4: voltage due to heating effects are determined using thermal regulation specification TCV_{OUT}
 - 5: Dropout voltage is defined as the input to output differential at which the output voltage drops 2% below its measured value with an applied input voltage of $V_{OUT(MAX)} + V_{DROPOUT(MAX)}$ or 2.7V, whichever is greater.
 - The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction to air (i.e., T_A , T_J , θ_{JA}). Exceeding the maximum allowable power dissipation will cause the device operating junction temperature to exceed the maximum 150°C rating. Sustained junction temperatures above 150°C can impact the device reliability.
 - The junction temperature is approximated by soaking the device under test at an ambient temperature equal to the desired Junction temperature. The test time is small enough such that the rise in the Junction temperature over the ambient temperature is not significant.

DC CHARACTERISTICS (CONTINUED)

Electrical Specifications: Unless otherwise specified, all limits are established for V_{IN} = V_{OUT(MAX)} + V_{DROPOUT(MAX)}, Note 1, I_{LOAD} = 100 μ A, C_{OUT} = 1 μ F (X7R), C_{IN} = 1 μ F (X7R), T_{A} = +25°C.

Boldface type applies for junction temperatures, T_{.1} (Note 7) of -40°C to +125°C.

Parameters	Symbol	Min	Тур	Max	Units	Conditions
Dropout Voltage	V _{DROPOUT}	_	330	650	mV	I _L = 250 mA, V _R = 5.0V
Note 1, Note 5		_	525	725	mV	I_L = 250 mA, 3.3V $\leq V_R < 5.0V$
		_	625	975	mV	I_L = 250 mA, 2.8V $\leq V_R < 3.3V$
		_	750	1100	mV	I_L = 250 mA, 2.5V \leq V_R $<$ 2.8V
		_	_	_	mV	V _R < 2.5V, See Maximum Output Current Parameter
Output Delay Time	T _{DELAY}	_	1000	_	μs	V_{IN} = 0V to 6V, V_{OUT} = 90% V_{R} , R_{L} = 50 Ω resistive
Output Noise	e _N	_	8		μV/(Hz) ^{1/2}	$I_L = 50 \text{ mA, } f = 1 \text{ kHz, } C_{OUT} = 1 \mu F$
Power Supply Ripple Rejection Ratio	PSRR	_	44	_	dB	$ f = 100 \text{ Hz}, \ C_{OUT} = 1 \ \mu\text{F}, \ I_L = 100 \ \mu\text{A}, \\ V_{INAC} = 100 \ \text{mV} \ \text{pk-pk}, \ C_{IN} = 0 \ \mu\text{F}, \\ V_R = 1.2 \text{V} $
Thermal Shutdown Protection	T _{SD}	_	150	_	°C	

- The minimum V_{IN} must meet two conditions: $V_{IN} \ge 2.7V$ and $V_{IN} \ge (V_{OUT(MAX)} + V_{DROPOUT(MAX)})$. Note
 - V_R is the nominal regulator output voltage. For example: $V_R = 1.2V$, 1.5V, 1.8V, 2.5V, 2.8V, 3.0V, 3.3V, 4.0V, or 5.0V.
 - The input voltage $V_{IN} = V_{OUT(MAX)} + V_{DROPOUT(MAX)}$ or $V_{IN} = 2.7V$ (whichever is greater); $I_{OUT} = 100 \ \mu A$. TCV_{OUT} = $(V_{OUT-HIGH} V_{OUT-LOW}) *10^6 / (V_R * \Delta Temperature)$, $V_{OUT-HIGH} = highest voltage measured over the temperature)$ ature range. V_{OUT-LOW} = lowest voltage measured over the temperature range
 - Load regulation is measured at a constant junction temperature using low duty cycle pulse testing. Changes in output voltage due to heating effects are determined using thermal regulation specification TCV_{OUT}.
 - Dropout voltage is defined as the input to output differential at which the output voltage drops 2% below its measured value with an applied input voltage of V_{OUT(MAX)} + V_{DROPOUT(MAX)} or 2.7V, whichever is greater.
 - The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction to air (i.e., T_A, T_J, θ_{JA}). Exceeding the maximum allowable power dissipation will cause the device operating junction temperature to exceed the maximum 150°C rating. Sustained junction temperatures above 150°C can impact the device reliability.
 - The junction temperature is approximated by soaking the device under test at an ambient temperature equal to the desired Junction temperature. The test time is small enough such that the rise in the Junction temperature over the ambient temperature is not significant.

TEMPERATURE SPECIFICATIONS

Parameters	Sym	Min	Тур	Max	Units	Conditions
Temperature Ranges						
Specified Temperature Range	T _A	-40		+125	°C	
Operating Temperature Range	T _A	-40		+125	°C	
Storage Temperature Range	T _A	-65		+150	°C	
Thermal Package Resistance						
Thermal Resistance, 3LD-SOT-223	θ _{JA} θ _{JC}	_	62 15	_	°C/W	EIA/JEDEC JESD51-7 FR-4 0.063 4-Layer Board
Thermal Resistance, 3LD-SOT-23A	θ_{JA} θ_{JC}	_	336 110	_	°C/W	EIA/JEDEC JESD51-7 FR-4 0.063 4-Layer Board
Thermal Resistance, 3LD-SOT-89	θ_{JA} θ_{JC}	_	75 10	_	°C/W	0.100 sq in copper on both sides of 2 sided board, with vias

The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction to air (i.e., T_A , θ_{JA}). Exceeding the maximum allowable power dissipation will cause the device operating junction temperature to exceed the maximum 150°C rating. Sustained junction temperatures above 150°C can impact the device reliability.

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated: V_R = 1.8V, C_{OUT} = 1 μF Ceramic (X7R), C_{IN} = 1 μF Ceramic (X7R), I_L = 100 μA , T_A = +25°C, V_{IN} = $V_{OUT(MAX)}$ + $V_{DROPOUT(MAX)}$ or 2.7V, whichever is greater.

Note: Junction Temperature (T_J) is approximated by soaking the device under test to an ambient temperature equal to the desired junction temperature. The test time is small enough such that the rise in Junction temperature over the Ambient temperature is not significant.

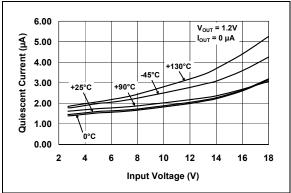


FIGURE 2-1: Quiescent Current vs. Input Voltage.

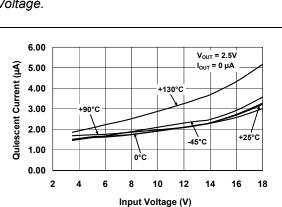


FIGURE 2-2: Quiescent Current vs. Input Voltage.

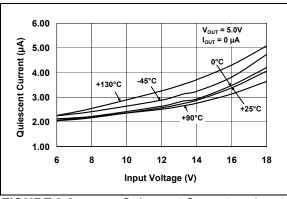


FIGURE 2-3: Quiescent Current vs. Input Voltage.

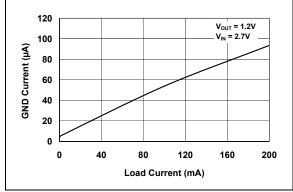


FIGURE 2-4: Ground Current vs. Load Current.

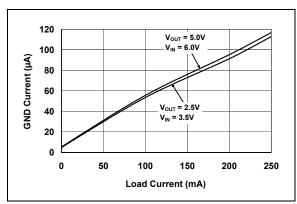


FIGURE 2-5: Ground Current vs. Load Current.

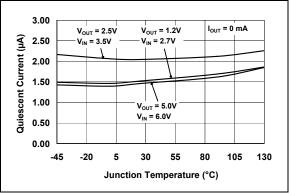


FIGURE 2-6: Quiescent Current vs. Junction Temperature.

Note: Unless otherwise indicated: V_R = 1.8V, C_{OUT} = 1 μF Ceramic (X7R), C_{IN} = 1 μF Ceramic (X7R), I_L = 100 μA , T_A = +25°C, V_{IN} = $V_{OUT(MAX)}$ + $V_{DROPOUT(MAX)}$ or 2.7V, whichever is greater.

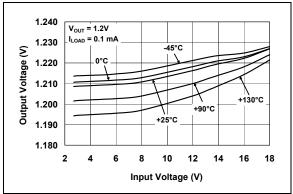


FIGURE 2-7: Output Voltage vs. Input Voltage.

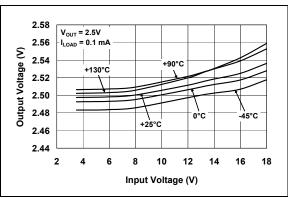


FIGURE 2-8: Output Voltage vs. Input Voltage.

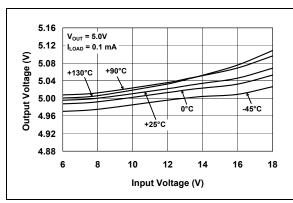


FIGURE 2-9: Output Voltage vs. Input Voltage.

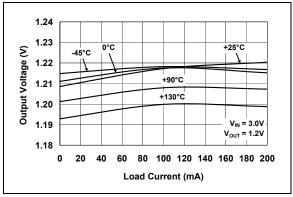


FIGURE 2-10: Output Voltage vs. Load Current.

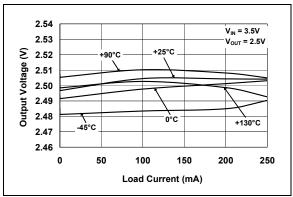


FIGURE 2-11: Output Voltage vs. Load Current.

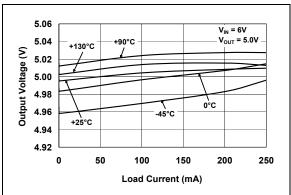


FIGURE 2-12: Output Voltage vs. Load Current.

Note: Unless otherwise indicated: V_R = 1.8V, C_{OUT} = 1 μF Ceramic (X7R), C_{IN} = 1 μF Ceramic (X7R), I_L = 100 μA , T_A = +25°C, V_{IN} = $V_{OUT(MAX)}$ + $V_{DROPOUT(MAX)}$ or 2.7V, whichever is greater.

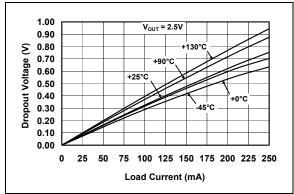


FIGURE 2-13: Dropout Voltage vs. Load Current.

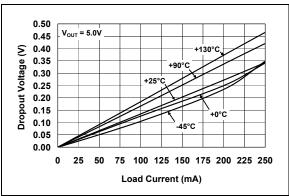


FIGURE 2-14: Dropout Voltage vs. Load Current.

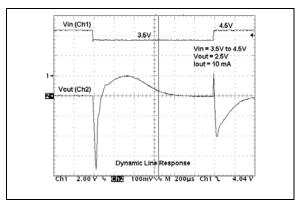


FIGURE 2-15: Dynamic Line Response.

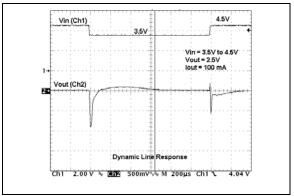


FIGURE 2-16: Dynamic Line Response.

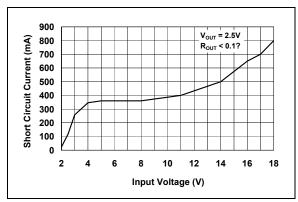


FIGURE 2-17: Short Circuit Current vs. Input Voltage.

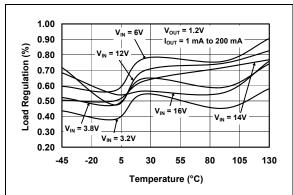


FIGURE 2-18: Load Regulation vs. Temperature.

Note: Unless otherwise indicated: V_R = 1.8V, C_{OUT} = 1 μF Ceramic (X7R), C_{IN} = 1 μF Ceramic (X7R), I_L = 100 μA , T_A = +25°C, V_{IN} = $V_{OUT(MAX)}$ + $V_{DROPOUT(MAX)}$ or 2.7V, whichever is greater.

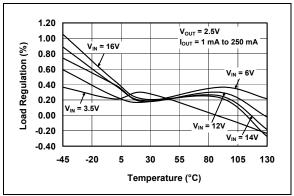


FIGURE 2-19: Load Regulation vs. Temperature.

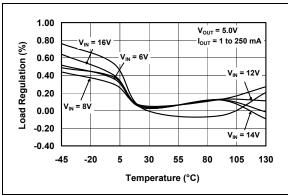


FIGURE 2-20: Load Regulation vs. Temperature.

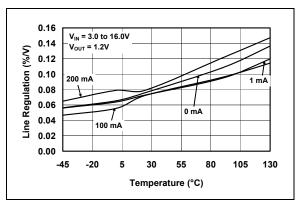


FIGURE 2-21: Line Regulation vs. Temperature.

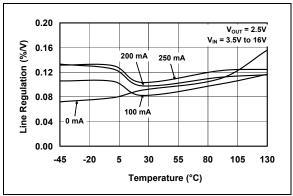


FIGURE 2-22: Line Regulation vs. Temperature.

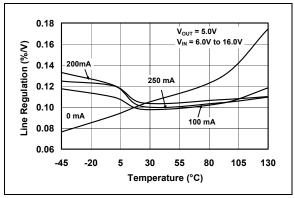


FIGURE 2-23: Line Regulation vs. Temperature.

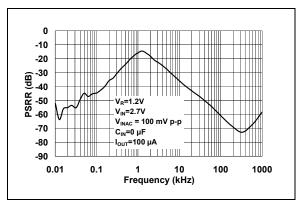


FIGURE 2-24: PSRR vs. Frequency.

Note: Unless otherwise indicated: V_R = 1.8V, C_{OUT} = 1 μF Ceramic (X7R), C_{IN} = 1 μF Ceramic (X7R), I_L = 100 μA, T_A = +25°C, V_{IN} = $V_{OUT(MAX)}$ + $V_{DROPOUT(MAX)}$ or 2.7V, whichever is greater.

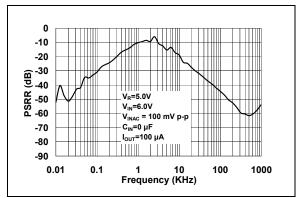


FIGURE 2-25: PSRR vs. Frequency.

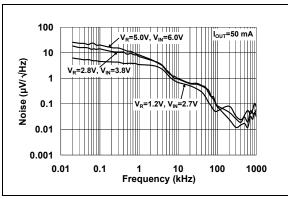


FIGURE 2-26: Output Noise vs. Frequency.

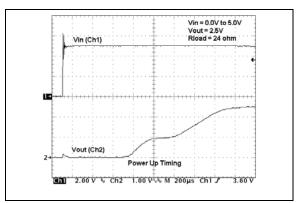


FIGURE 2-27: Power Up Timing.

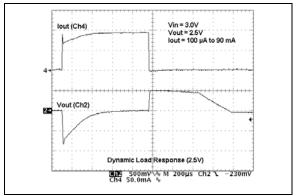


FIGURE 2-28: Dynamic Load Response.

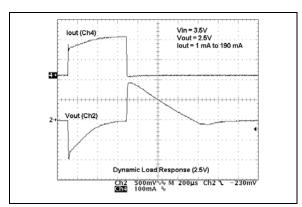


FIGURE 2-29: Dynamic Load Response.

3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

TABLE 3-1: MCP1703 PIN FUNCTION TABLE

Pin No. SOT-223-3	Pin No. SOT-23A	Pin No. SOT-89-3	Name	Function	
2	1	1	GND	Ground Terminal	
3	2	3	V _{OUT}	Regulated Voltage Output	
1	3	2,Tab	V _{IN}	Unregulated Supply Voltage	
	-	-	NC	No connection	

3.1 Ground Terminal (GND)

Regulator ground. Tie GND to the negative side of the output and the negative side of the input capacitor. Only the LDO bias current (2.0 μA typical) flows out of this pin; there is no high current. The LDO output regulation is referenced to this pin. Minimize voltage drops between this pin and the negative side of the load.

3.2 Regulated Output Voltage (V_{OUT})

Connect V_{OUT} to the positive side of the load and the positive terminal of the output capacitor. The positive side of the output capacitor should be physically located as close to the LDO V_{OUT} pin as is practical. The current flowing out of this pin is equal to the DC load current.

3.3 Unregulated Input Voltage (V_{IN})

Connect V_{IN} to the input unregulated source voltage. Like all low dropout linear regulators, low source impedance is necessary for the stable operation of the LDO. The amount of capacitance required to ensure low source impedance will depend on the proximity of the input source capacitors or battery type. For most applications, 1 μ F of capacitance will ensure stable operation of the LDO circuit. For applications that have load currents below 100 mA, the input capacitance requirement can be lowered. The type of capacitor used can be ceramic, tantalum or aluminum electrolytic. The low ESR characteristics of the ceramic will yield better noise and PSRR performance at high-frequency.

4.0 DETAILED DESCRIPTION

4.1 Output Regulation

A portion of the LDO output voltage is fed back to the internal error amplifier and compared with the precision internal band-gap reference. The error amplifier output will adjust the amount of current that flows through the P-Channel pass transistor, thus regulating the output voltage to the desired value. Any changes in input voltage or output current will cause the error amplifier to respond and adjust the output voltage to the target voltage (refer to Figure 4-1).

4.2 Overcurrent

The MCP1703 internal circuitry monitors the amount of current flowing through the P-Channel pass transistor. In the event of a short-circuit or excessive output current, the MCP1703 will turn off the P-Channel device for a short period, after which the LDO will attempt to restart. If the excessive current remains, the cycle will repeat itself.

4.3 Overtemperature

The internal power dissipation within the LDO is a function of input-to-output voltage differential and load current. If the power dissipation within the LDO is excessive, the internal junction temperature will rise above the typical shutdown threshold of 150°C. At that point, the LDO will shut down and begin to cool to the typical turn-on junction temperature of 130°C. If the power dissipation is low enough, the device will continue to cool and operate normally. If the power dissipation remains high, the thermal shutdown protection circuitry will again turn off the LDO, protecting it from catastrophic failure.

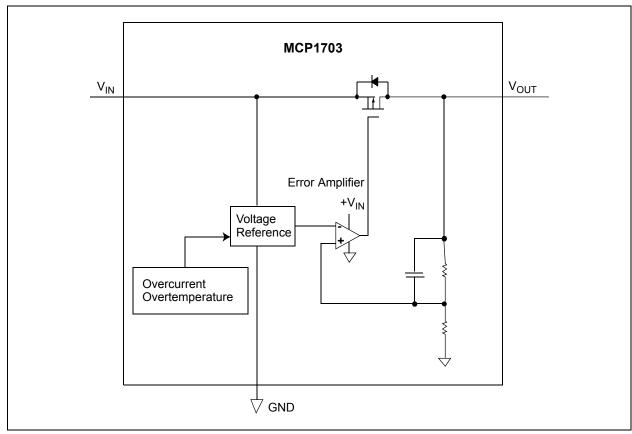


FIGURE 4-1: Block Diagram.

5.0 FUNCTIONAL DESCRIPTION

The MCP1703 CMOS low dropout linear regulator is intended for applications that need the lowest current consumption while maintaining output voltage regulation. The operating continuous load range of the MCP1703 is from 0 mA to 250 mA ($V_R \geq 2.5V$). The input operating voltage range is from 2.7V to 16.0V, making it capable of operating from two or more alkaline cells or single and multiple Li-lon cell batteries.

5.1 Input

The input of the MCP1703 is connected to the source of the P-Channel PMOS pass transistor. As with all LDO circuits, a relatively low source impedance (10 Ω) is needed to prevent the input impedance from causing the LDO to become unstable. The size and type of the capacitor needed depends heavily on the input source type (battery, power supply) and the output current range of the application. For most applications (up to 100 mA), a 1 μ F ceramic capacitor will be sufficient to ensure circuit stability. Larger values can be used to improve circuit AC performance.

5.2 Output

The maximum rated continuous output current for the MCP1703 is 250 mA ($V_R \ge 2.5V$). For applications where $V_R < 2.5V$, the maximum output current is 200 mA.

A minimum output capacitance of 1.0 μF is required for small signal stability in applications that have up to 250 mA output current capability. The capacitor type can be ceramic, tantalum or aluminum electrolytic. The esr range on the output capacitor can range from 0Ω to 2.0Ω .

5.3 Output Rise time

When powering up the internal reference output, the typical output rise time of $1000\,\mu s$ is controlled to prevent overshoot of the output voltage.

6.0 APPLICATION CIRCUITS & ISSUES

6.1 Typical Application

The MCP1703 is most commonly used as a voltage regulator. Its low quiescent current and low dropout voltage make it ideal for many battery-powered applications.

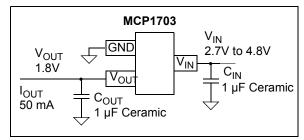


FIGURE 6-1: Typical Application Circuit.

6.1.1 APPLICATION INPUT CONDITIONS

Package Type = SOT-23A

Input Voltage Range = 2.7V to 4.8V

 V_{IN} maximum = 4.8V V_{OUT} typical = 1.8V

 $I_{OLIT} = 50 \text{ mA maximum}$

6.2 Power Calculations

6.2.1 POWER DISSIPATION

The internal power dissipation of the MCP1703 is a function of input voltage, output voltage and output current. The power dissipation, as a result of the quiescent current draw, is so low, it is insignificant (2.0 $\mu A \times V_{\text{IN}}$). The following equation can be used to calculate the internal power dissipation of the LDO.

EQUATION 6-1:

$$P_{LDO} = (V_{IN(MAX))} - V_{OUT(MIN)}) \times I_{OUT(MAX))}$$

P_{LDO} = LDO Pass device internal power dissipation

 $V_{IN(MAX)}$ = Maximum input voltage

V_{OUT(MIN)} = LDO minimum output voltage

The maximum continuous operating junction temperature specified for the MCP1703 is +125°C. To estimate the internal junction temperature of the MCP1703, the total internal power dissipation is multiplied by the thermal resistance from junction to ambient (R θ_{JA}). The thermal resistance from junction to ambient for the SOT-23A pin package is estimated at 336°C/W.

EQUATION 6-2:

$$T_{J(MAX)} = P_{TOTAL} \times R\theta_{JA} + T_{AMAX}$$

Where:

 $T_{J(MAX)}$ = Maximum continuous junction

temperature

P_{TOTAL} = Total device power dissipation

 $R\theta_{JA}$ = Thermal resistance from junction-

to-ambient

T_{AMAX} = Maximum ambient temperature

The maximum power dissipation capability for a package can be calculated given the junction-to-ambient thermal resistance and the maximum ambient temperature for the application. The following equation can be used to determine the package maximum internal power dissipation.

EQUATION 6-3:

$$P_{D(MAX)} = \frac{(T_{J(MAX)} - T_{A(MAX)})}{R\theta_{JA}}$$

Where:

 $P_{D(MAX)}$ = Maximum device power dissipation

 $T_{J(MAX)}$ = Maximum continuous junction

temperature

 $T_{A(MAX)}$ = Maximum ambient temperature

 $R\theta_{JA}$ = Thermal resistance from junction-

to-ambient

EQUATION 6-4:

$$T_{I(RISE)} = P_{D(MAX)} \times R\theta_{IA}$$

Where:

T_{J(RISE)} = Rise in device junction temperature over the ambient temperature

P_{TOTAL} = Maximum device power dissipation

 $R\theta_{JA}$ = Thermal resistance from junction to

EQUATION 6-5:

$$T_J = T_{J(RISE)} + T_A$$

Where:

 $T_{.I}$ = Junction Temperature

 $T_{J(RISE)}$ = Rise in device junction temperature

over the ambient temperature

 T_A = Ambient temperature

6.3 Voltage Regulator

Internal power dissipation, junction temperature rise, junction temperature and maximum power dissipation are calculated in the following example. The power dissipation, as a result of ground current, is small enough to be neglected.

6.3.1 POWER DISSIPATION EXAMPLE

Package

Package Type = SOT-23A Input Voltage

 $V_{IN} = 2.7V \text{ to } 4.8V$

LDO Output Voltages and Currents

 $V_{OUT} = 1.8V$ $I_{OUT} = 50 \text{ mA}$

Maximum Ambient Temperature

 $T_{A(MAX)} = +40^{\circ}C$

Internal Power Dissipation

Internal Power dissipation is the product of the LDO output current times the voltage across the LDO $(V_{\text{IN}}$ to $V_{\text{OUT}})$.

 $P_{LDO(MAX)} = (V_{IN(MAX)} - V_{OUT(MIN)}) \times I_{OUT(MAX)}$ $P_{LDO} = (4.8V - (0.97 \times 1.8V)) \times 50 \text{ mA}$

P_{LDO} = 152.7 milli-Watts

Device Junction Temperature Rise

The internal junction temperature rise is a function of internal power dissipation and the thermal resistance from junction to ambient for the application. The thermal resistance from junction to ambient (R0,1A) is derived from an EIA/JEDEC standard for measuring thermal resistance for small surface mount packages. The EIA/ JEDEC specification is JESD51-7, "High Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages". The standard describes the test method and board specifications for measuring the thermal resistance from junction to ambient. The actual thermal resistance for a particular application can vary depending on many factors, such as copper area and thickness. Refer to AN792, "A Method to Determine How Much Power a SOT23 Can Dissipate in an Application", (DS00792), for more information regarding this subject.

 $T_{J(RISE)} = P_{TOTAL} x Rq_{JA}$

T_{JRISE} = 152.7 milli-Watts x 336.0°C/Watt

 $T_{JRISE} = 51.3$ °C

Junction Temperature Estimate

To estimate the internal junction temperature, the calculated temperature rise is added to the ambient or offset temperature. For this example, the worst-case junction temperature is estimated below.

$$T_J = T_{JRISE} + T_{A(MAX)}$$

 $T_J = 91.3$ °C

Maximum Package Power Dissipation at +40°C Ambient Temperature

SOT-23A (336.0°C/Watt = $R\theta_{JA}$)

 $P_{D(MAX)} = (125^{\circ}C - 40^{\circ}C) / 336^{\circ}C/W$

 $P_{D(MAX)} = 253 \text{ milli-Watts}$

SOT-89 (75°C/Watt = $R\theta_{JA}$)

 $P_{D(MAX)} = (125^{\circ}C - 40^{\circ}C) / 75^{\circ}C/W$

 $P_{D(MAX)} = 1.133 \text{ Watts}$

SOT-223 (62.9°C/Watt = $R\theta_{JA}$)

 $P_{D(MAX)} = (125^{\circ}C - 40^{\circ}C) / 62.9^{\circ}C/W$

 $P_{D(MAX)} = 1.35 \text{ Watts}$

6.4 Voltage Reference

The MCP1703 can be used not only as a regulator, but also as a low quiescent current voltage reference. In many microcontroller applications, the initial accuracy of the reference can be calibrated using production test equipment or by using a ratio measurement. When the initial accuracy is calibrated, the thermal stability and line regulation tolerance are the only errors introduced by the MCP1703 LDO. The low-cost, low quiescent current and small ceramic output capacitor are all advantages when using the MCP1703 as a voltage reference.

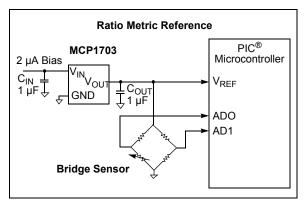


FIGURE 6-2: Using the MCP1703 as a Voltage Reference.

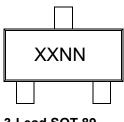
6.5 Pulsed Load Applications

For some applications, there are pulsed load current events that may exceed the specified 250 mA maximum specification of the MCP1703. The internal current limit of the MCP1703 will prevent high peak load demands from causing non-recoverable damage. The 250 mA rating is a maximum average continuous rating. As long as the average current does not exceed 250 mA, pulsed higher load currents can be applied to the MCP1703. The typical current limit for the MCP1703 is 500 mA ($T_A + 25^{\circ}$ C).

7.0 PACKAGING INFORMATION

7.1 **Package Marking Information**

3-Pin SOT-23A



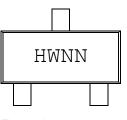
3-Lead SOT-89



Standard Options for SOT-23A and SOT-89								
	Extended Temp							
Symbol Voltage * Symbol Voltage *								
HM	1.2	HT	3.0					
HP	1.5	HU	3.3					
HQ	1.8	HV	4.0					
HR	2.5	HW	5.0					
HS	2.8	_	_					
* C	tout valtages	بمجيب ملطماني						

Custom output voltages available upon request. Contact your local Microchip sales office for more information.

Example:



Example



3-Lead SOT-223

Tab is GND



Standard	Options	for SOT-223

	Extended Temp						
Symbol	Voltage *	Symbol	Voltage *				
12	1.2	30	3.0				
15	1.5	33	3.3				
18	1.8	40	4.0				
25	2.5	50	5.0				
28	2.8	_	_				

^{*} Custom output voltages available upon request. Contact your local Microchip sales office for more information.

Example:

Tab is GND



Legend: XX...X Customer-specific information

Year code (last digit of calendar year) Year code (last 2 digits of calendar year) ΥY WW Week code (week of January 1 is week '01')

NNN Alphanumeric traceability code

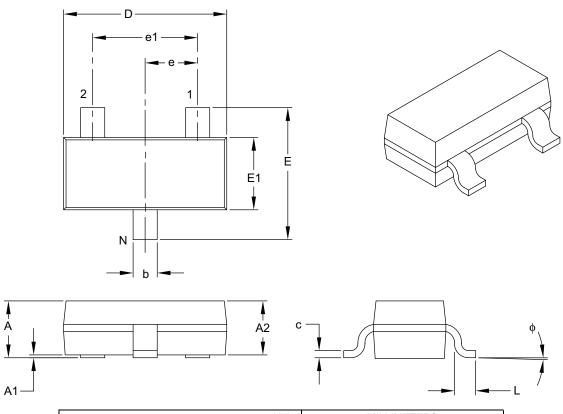
(e3) Pb-free JEDEC designator for Matte Tin (Sn)

> This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.

In the event the full Microchip part number cannot be marked on one line, it will Note: be carried over to the next line, thus limiting the number of available characters for customer-specific information.

3-Lead Plastic Small Outline Transistor (CB) [SOT-23A]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units		MILLIMETERS		
	Dimension Limits	MIN	NOM	MAX	
Number of Pins	N		3		
Lead Pitch	е		0.95 BSC		
Outside Lead Pitch	e1		1.90 BSC		
Overall Height	A	0.89	-	1.45	
Molded Package Thickness	A2	0.90	_	1.30	
Standoff	A1	0.00	_	0.15	
Overall Width	E	2.10	-	3.00	
Molded Package Width	E1	1.20	_	1.80	
Overall Length	D	2.70	_	3.10	
Foot Length	L	0.15	_	0.60	
Foot Angle	ф	0°	-	30°	
Lead Thickness	С	0.09	_	0.26	
Lead Width	b	0.30	_	0.51	

Notes:

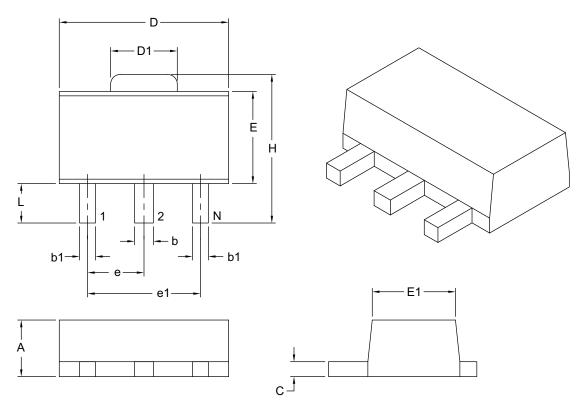
- 1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
- 2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-130B

3-Lead Plastic Small Outline Transistor Header (MB) [SOT-89]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS		
Dimension	n Limits	MIN	MAX
Number of Leads	N	(3
Pitch	е	1.50	BSC
Outside Lead Pitch	e1	3.00	BSC
Overall Height	Α	1.40	1.60
Overall Width	Н	3.94	4.25
Molded Package Width at Base	Е	2.29	2.60
Molded Package Width at Top	E1	2.13	2.29
Overall Length	D	4.39	4.60
Tab Length	D1	1.40	1.83
Foot Length	L	0.79	1.20
Lead Thickness	С	0.35	0.44
Lead 2 Width	b	0.41	0.56
Leads 1 & 3 Width	b1	0.36	0.48

Notes:

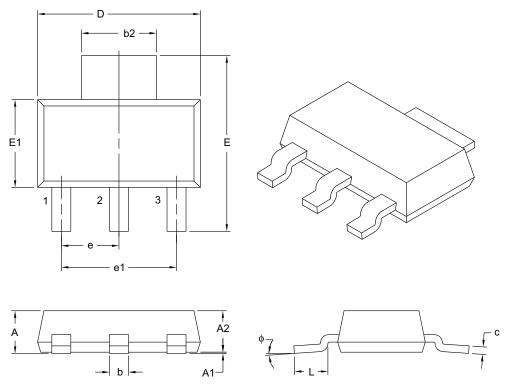
- 1. Dimensions D and E do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
- 2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-029B

3-Lead Plastic Small Outline Transistor (DB) [SOT-223]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units		MILLIMETERS		
	Dimension Limits	MIN	NOM	MAX	
Number of Leads	N		3	•	
Lead Pitch	е		2.30 BSC		
Outside Lead Pitch	e1		4.60 BSC		
Overall Height	A	1.80			
Standoff	A1	0.02	-	0.10	
Molded Package Height	A2	1.50	1.60	1.70	
Overall Width	E	6.70	7.00	7.30	
Molded Package Width	E1	3.30	3.50	3.70	
Overall Length	D	6.30	6.50	6.70	
Lead Thickness	С	0.23	0.30	0.35	
Lead Width	b	0.60	0.76	0.84	
Tab Lead Width	b2	2.90	3.00	3.10	
Foot Length	L	0.75	_	_	
Lead Angle	ф	0°	_	10°	

Notes:

- 1. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.127 mm per side.
- 2. Dimensioning and tolerancing per ASME Y14.5M.

 ${\it BSC: Basic Dimension. Theoretically exact value shown without tolerances.}$

Microchip Technology Drawing C04-032B

APPENDIX A: REVISION HISTORY

Revision A (June 2007)

• Original Release of this Document.

MCP1703

NOTES:

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO. X- XX X X X/ XX Device Tape Output Feature Tolerance Temp. Package and Reel Voltage Code

Device: MCP1703: 250 mA, 16V Low Quiescent Current LDO

Tape and Reel: T = Tape and Reel

Output Voltage *: 12 = 1.2V "Standard"

15 = 1.5V "Standard" 18 = 1.8V "Standard" 25 = 2.5V "Standard" 28 = 2.8V "Standard" 30 = 3.0V "Standard" 33 = 3.3V "Standard" 40 = 4.0V "Standard" 50 = 5.0V "Standard"

*Contact factory for other output voltage options.

Extra Feature Code: 0 = Fixed

Tolerance: 2 = 2.0% (Standard)

Temperature: E = -40° C to $+125^{\circ}$ C

Package Type: CB = Plastic Small Outline Transistor (SOT-23A) 3-lead,

DB = Plastic Small Outline Transistor (SOT-223) 3-lead,

MB = Plastic Small Outline Transistor (SOT-89) 3-lead,

Examples:

a) MCP1703T-1202E/XX: Tape and Reel, 1.2V

b) MCP1703T-1502E/XX: Tape and Reel, 1.5V

c) MCP1703T-1802E/XX: Tape and Reel, 1.8V

d) MCP1703T-2502E/XX: Tape and Reel, 2.5V

e) MCP1703T-2802E/XX: Tape and Reel, 2.8V

f) MCP1703T-3002E/XX: Tape and Reel, 3.0V

g) MCP1703T-3302E/XX: Tape and Reel, 3.3V

h) MCP1703T-3602E/XX: Tape and Reel, 3.6V

i) MCP1703T-4002E/XX: Tape and Reel, 4.0V

j) MCP1703T-5002E/XX: Tape and Reel, 5.0V

XX = CB for 3LD SOT-23A package

= DB for 3LD SOT-223 package

= MB for 3LD SOT-89 package

MCP1703

NOTES:

Note the following details of the code protection feature on Microchip devices:

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our
 knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data
 Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

Code protection is constantly evolving. We at Microchip are committed to continuously improving the code protection features of our products. Attempts to break Microchip's code protection feature may be a violation of the Digital Millennium Copyright Act. If such acts allow unauthorized access to your software or other copyrighted work, you may have a right to sue for relief under that Act.

Information contained in this publication regarding device applications and the like is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. MICROCHIP MAKES NO REPRESENTATIONS OR WARRANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION, INCLUDING BUT NOT LIMITED TO ITS CONDITION, QUALITY, PERFORMANCE, MERCHANTABILITY OR FITNESS FOR PURPOSE. Microchip disclaims all liability arising from this information and its use. Use of Microchip devices in life support and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend, indemnify and hold harmless Microchip from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights.

Trademarks

The Microchip name and logo, the Microchip logo, Accuron, dsPIC, KEELOQ, KEELOQ logo, microID, MPLAB, PIC, PICmicro, PICSTART, PRO MATE, rfPIC and SmartShunt are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

AmpLab, FilterLab, Linear Active Thermistor, Migratable Memory, MXDEV, MXLAB, SEEVAL, SmartSensor and The Embedded Control Solutions Company are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Analog-for-the-Digital Age, Application Maestro, CodeGuard, dsPICDEM, dsPICDEM.net, dsPICworks, ECAN, ECONOMONITOR, FanSense, FlexROM, fuzzyLAB, In-Circuit Serial Programming, ICSP, ICEPIC, Mindi, MiWi, MPASM, MPLAB Certified logo, MPLIB, MPLINK, PICkit, PICDEM, PICDEM.net, PICLAB, PICtail, PowerCal, PowerInfo, PowerMate, PowerTool, REAL ICE, rfLAB, Select Mode, Smart Serial, SmartTel, Total Endurance, UNI/O, WiperLock and ZENA are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

SQTP is a service mark of Microchip Technology Incorporated in the U.S.A.

All other trademarks mentioned herein are property of their respective companies.

© 2007, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.

Printed on recycled paper.

QUALITY MANAGEMENT SYSTEM

CERTIFIED BY DNV

ISO/TS 16949:2002

Microchip received ISO/TS-16949:2002 certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona; Gresham, Oregon and design centers in California and India. The Company's quality system processes and procedures are for its PIC® MCUs and dsPIC® DSCs, KEELOQ® code hopping devices, Serial EEPROMs, microperipherals, nonvolatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001:2000 certified.



WORLDWIDE SALES AND SERVICE

AMERICAS

Corporate Office

2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200

Fax: 480-792-7277 Technical Support:

http://support.microchip.com

Web Address: www.microchip.com

Atlanta

Duluth, GA Tel: 678-957-9614 Fax: 678-957-1455

Roston

Westborough, MA Tel: 774-760-0087 Fax: 774-760-0088

Chicago Itasca, IL

Tel: 630-285-0071 Fax: 630-285-0075

Dallas

Addison, TX Tel: 972-818-7423 Fax: 972-818-2924

Detroit

Farmington Hills, MI Tel: 248-538-2250 Fax: 248-538-2260

Kokomo

Kokomo, IN Tel: 765-864-8360 Fax: 765-864-8387

Los Angeles

Mission Viejo, CA Tel: 949-462-9523 Fax: 949-462-9608

Santa Clara

Santa Clara, CA Tel: 408-961-6444 Fax: 408-961-6445

Toronto

Mississauga, Ontario, Canada

Tel: 905-673-0699 Fax: 905-673-6509

ASIA/PACIFIC

Asia Pacific Office

Suites 3707-14, 37th Floor Tower 6, The Gateway Habour City, Kowloon Hong Kong

Tel: 852-2401-1200 Fax: 852-2401-3431

Australia - Sydney Tel: 61-2-9868-6733 Fax: 61-2-9868-6755

China - Beijing

Tel: 86-10-8528-2100 Fax: 86-10-8528-2104

China - Chengdu Tel: 86-28-8665-5511 Fax: 86-28-8665-7889

China - Fuzhou

Tel: 86-591-8750-3506 Fax: 86-591-8750-3521

China - Hong Kong SAR

Tel: 852-2401-1200 Fax: 852-2401-3431

China - Qingdao

Tel: 86-532-8502-7355 Fax: 86-532-8502-7205

China - Shanghai

Tel: 86-21-5407-5533 Fax: 86-21-5407-5066

China - Shenyang

Tel: 86-24-2334-2829 Fax: 86-24-2334-2393

China - Shenzhen

Tel: 86-755-8203-2660 Fax: 86-755-8203-1760

China - Shunde

Tel: 86-757-2839-5507 Fax: 86-757-2839-5571

China - Wuhan

Tel: 86-27-5980-5300 Fax: 86-27-5980-5118

China - Xian

Tel: 86-29-8833-7250 Fax: 86-29-8833-7256

ASIA/PACIFIC

India - Bangalore

Tel: 91-80-4182-8400 Fax: 91-80-4182-8422

India - New Delhi

Tel: 91-11-4160-8631 Fax: 91-11-4160-8632

India - Pune

Tel: 91-20-2566-1512 Fax: 91-20-2566-1513

Japan - Yokohama

Tel: 81-45-471- 6166 Fax: 81-45-471-6122

Korea - Gumi

Tel: 82-54-473-4301 Fax: 82-54-473-4302

Korea - Seoul

Tel: 82-2-554-7200 Fax: 82-2-558-5932 or 82-2-558-5934

Malaysia - Penang Tel: 60-4-646-8870

Fax: 60-4-646-5086

Philippines - Manila

Tel: 63-2-634-9065 Fax: 63-2-634-9069

Singapore Tel: 65-6334-8870

Fax: 65-6334-8850 Taiwan - Hsin Chu Tel: 886-3-572-9526

Fax: 886-3-572-6459 Taiwan - Kaohsiung

Tel: 886-7-536-4818 Fax: 886-7-536-4803

Taiwan - Taipei

Tel: 886-2-2500-6610 Fax: 886-2-2508-0102

Thailand - Bangkok Tel: 66-2-694-1351

Fax: 66-2-694-1350

EUROPE

Austria - Wels

Tel: 43-7242-2244-39 Fax: 43-7242-2244-393 Denmark - Copenhagen

Tel: 45-4450-2828 Fax: 45-4485-2829

France - Paris

Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

Germany - Munich

Tel: 49-89-627-144-0 Fax: 49-89-627-144-44

Italy - Milan

Tel: 39-0331-742611 Fax: 39-0331-466781

Netherlands - Drunen Tel: 31-416-690399

Fax: 31-416-690340 Spain - Madrid

Tel: 34-91-708-08-90

Fax: 34-91-708-08-91 UK - Wokingham

Tel: 44-118-921-5869 Fax: 44-118-921-5820

12/08/06